



# *27<sup>th</sup> ArbeitsKreis Bipolar*

*Crolles, France, October 24, 2014*

<b>08:30 - 08:45</b>		<b>Arrival</b>	
<b>08:45 - 08:50</b>	<b>Opening</b>	<b>ST</b>	<b>D. Céli</b>
<b>08:50 - 09:10</b>	<b>Member matters</b>	<b>Infineon</b>	<b>J. Berkner</b>
<b>09:10 - 9:50</b>	<b>Automated Transit Time and Transfer Current Extraction</b>	<b>ST/IMS/TuD</b>	<b>T. Rosenbaum</b>
<b>09:50 - 10:30</b>	<b>Semiconductor Noise in the Time and Frequency Domain</b>	<b>SisConsult</b>	<b>F. Sischka</b>
<b>10:30 - 10:45</b>		<b>Break</b>	
<b>10:45 - 11:25</b>	<b>Parasitic Bipolar Modeling for Voltage Scalable MOSFET Transistors</b>	<b>AMS</b>	<b>M. Tang</b>
<b>11:25 - 12:05</b>	<b>Bondwire Inductance. Calculation and Measurements</b>	<b>Infineon</b>	<b>J. Berkner</b>
<b>12:05 - 12:45</b>	<b>Investigation on Transient Intra-Device Thermal Coupling</b>	<b>IMS</b>	<b>R. Desposito</b>
<b>12:45 - 14:00</b>		<b>Lunch</b>	
<b>14:00 - 14:15</b>	<b>HICUM/L2 Status</b>	<b>TuD</b>	<b>A. Pawlak</b>
<b>14:15 - 15:00</b>	<b>Investigation on Bias Dependence of Critical Current in HICUM Models</b>	<b>ST</b>	<b>D. Céli</b>
<b>15:00 - 15:45</b>	<b>Experiences with HICUM/L2 v2.32</b>	<b>ST</b>	<b>N. Derrier</b>
<b>15:45 - 16:05</b>		<b>Break</b>	
<b>16:05 - 16:45</b>	<b>Barrier Model and Extraction</b>	<b>ST/IMS/TuD</b>	<b>T. Rosenbaum</b>
<b>16:45 - 17:00</b>		<b>Conclusion and End of the Workshop</b>	